Technical Data *Green Products*
Data Sheet N1708, Rev. -

SB520/SB530/SB550 SCHOTTKY RECTIFIER

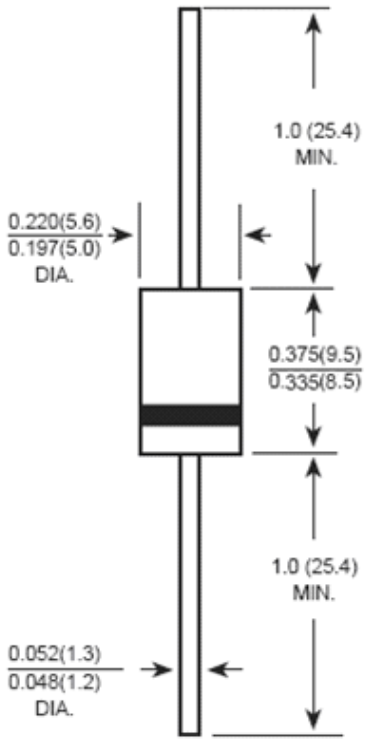
Applications:

- **Switching power supply**
- **Converters**
- **Free-Wheeling diodes**
- **Reverse battery protection**
- **Disk drives**
- **Battery charging**

Features:

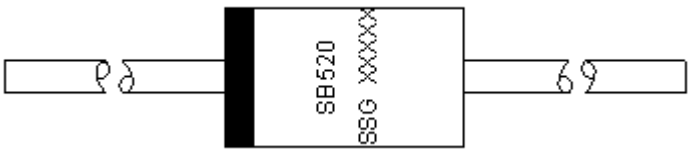
- **Schottky Barrier Chip**
- **Guard Ring Die Construction for Transient Protection**
- **High Current Capability**
- **Low Power Loss, High Efficiency**
- **High Surge Current Capability**
- **For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications**
- **This is a Pb − Free Device**
- **All SMC parts are traceable to the wafer lot**
- **Additional testing can be offered upon request**

Mechanical Dimensions: In Inches / mm



DO-201AD

Marking Diagram:



Where XXXXX is YYWWL

SB = Device Type
5 = Forward Current (5A)
20 = Reverse Voltage (20V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions：Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SB520-SB550	DO-201AD (Pb-Free)	1250 pcs / Tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	SB520	SB530	SB550	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	50	V
Average Rectified Output Current (Note 1) @T_L = 100°C	Io	5.0			A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	120			A
Forward Voltage @I_F =5.0A	V_{FM}	0.55		0.70	V
Peak Reverse Current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I_{RM}	0.5 20			mA
Typical Junction Capacitance (Note 2) @V_R = 5V	Cj	550		400	pF
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	25			K/W
Typical Thermal Resistance Junction to Lead (Note 3)	$R_{\theta JL}$	8			K/W
Junction Temperature	T_J	-55 to +150			°C
Storage Temperature Range	T_{STG}	-55 to +150			°C
Approximate Weight	wt	1.02			g
Case Style	DO-201AD				

Note:1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.
3. Thermal resistance junction to lead vertical P.C.B. mounted, 0.375” (9.5mm) lead length.

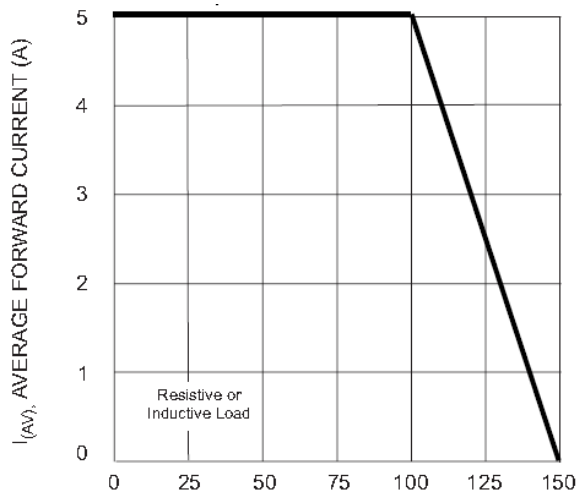


Fig. 1 Forward Current Derating Curve

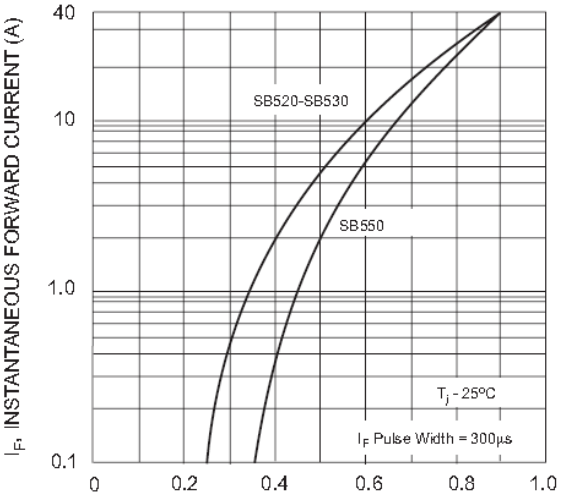


Fig. 2 Typical Forward Characteristics

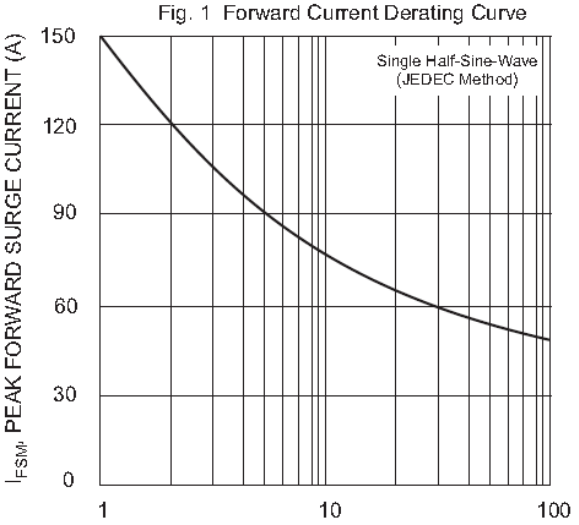


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

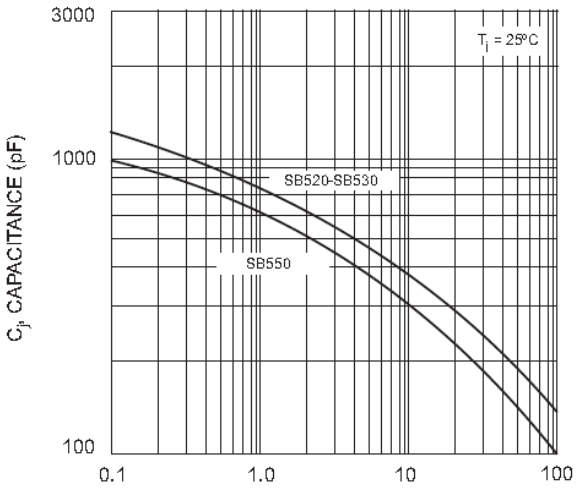


Fig. 4 Typical Junction Capacitance

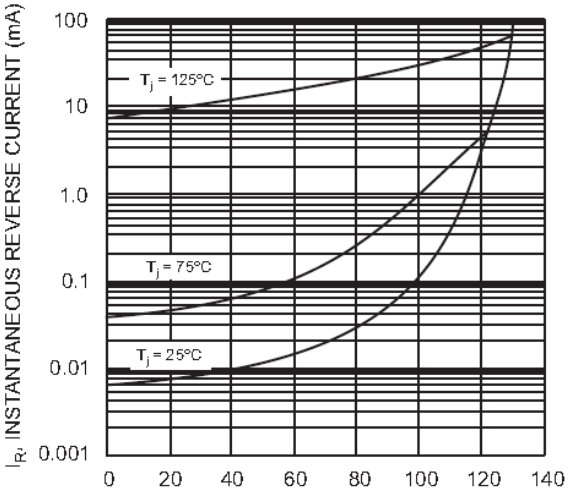


Fig. 5 Typical Reverse Characteristics

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